NTLUS3A90PZ

MOSFET – Power, Single, P-Channel, ESD, µCool, UDFN, 1.6x1.6x0.55 mm

-20 V, -5.0 A

ON Semiconductor®

http://onsemi.com

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 1.6x1.6x0.55 mm for Board Space Saving
- Lowest RDS(on) in 1.6x1.6 Package
- ESD Protected
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Load Switch
- PA Switch and Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others
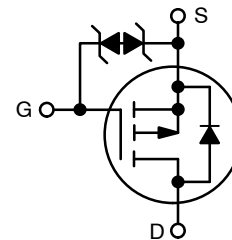
MOSFET

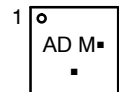| $V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
−20 V	62 mΩ @ −4.5 V	−5.0 A
	95 mΩ @ −2.5 V	
	140 mΩ @ −1.8 V	
	230 mΩ @ −1.5 V	

P−Channel MOSFET
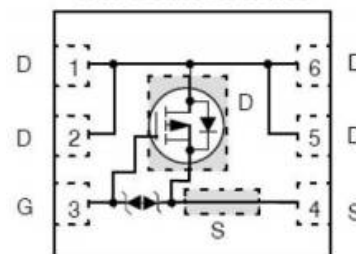
MARKING DIAGRAM

UDFN6
CASE 517AU
µCOOL™

AD = Specific Device Code
M = Date Code
■ = Pb−Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS

(Top View)

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	−20	V
Gate-to-Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−4.0	A
		T_A = 85°C		−2.9	
	$t \leq 5$ s	T_A = 25°C		−5.0	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	1.5	W
	$t \leq 5$ s	T_A = 25°C		2.3	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	−2.6	A
		T_A = 85°C		−1.9	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.6	W
Pulsed Drain Current		tp = 10 µs	I_{DM}	−17	A
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	°C
Source Current (Body Diode) (Note 2)			I_S	−0.84	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

May, 2019 − Rev. 2

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient − Steady State (Note 3)	$R_{\theta JA}$	84	°C/W
Junction-to-Ambient − t ≤ 5 s (Note 3)	$R_{\theta JA}$	55	
Junction-to-Ambient − Steady State min Pad (Note 4)	$R_{\theta JA}$	200	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Units
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = −250 μA, ref to 25°C			−8.0		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −20 V	T_J = 25°C			−1.0	μA
			T_J = 85°C			−10	
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V				±10	μA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.4		−1.0	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$				3.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −4.0 A			54	62	mΩ
		V_{GS} = −2.5 V, I_D = −2.0 A			74	95	
		V_{GS} = −1.8 V, I_D = −1.2 A			104	140	
		V_{GS} = −1.5 V, I_D = −0.5 A			137	230	
Forward Transconductance	g_{FS}	V_{DS} = −10 V, I_D = −3.0 A			10		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −10 V			950		pF
Output Capacitance	C_{OSS}				90		
Reverse Transfer Capacitance	C_{RSS}				85		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −10 V; I_D = −3.0 A			12.3		nC
Threshold Gate Charge	$Q_{G(TH)}$				0.9		
Gate-to-Source Charge	Q_{GS}				1.6		
Gate-to-Drain Charge	Q_{GD}				3.3		
SWITCHING CHARACTERISTICS, VGS = 4.5 V (Note 6)							
Turn-On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −10 V, I_D = −3.0 A, R_G = 1 Ω			7.9		ns
Rise Time	t_r				15.7		
Turn-Off Delay Time	$t_{d(OFF)}$				34.8		
Fall Time	t_f				28.5		
DRAIN-SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	VSD	V_{GS} = 0 V, I_S = −1.0 A	T_J = 25°C		0.74	1.2	V
			T_J = 125°C		0.62		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dis/dt = 100 A/μs, I_S = −1.0 A			11.8		ns
Charge Time	t_a				8.5		
Discharge Time	t_b				3.3		
Reverse Recovery Charge	Q_{RR}				6.0		nC

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.
5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

NTLUS3A90PZ

TYPICAL CHARACTERISTICS

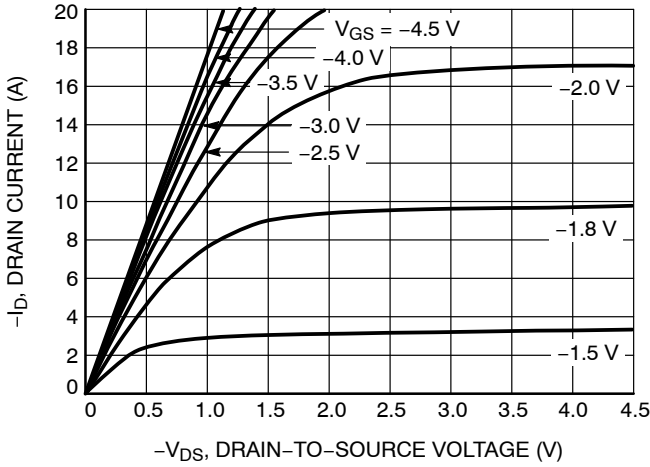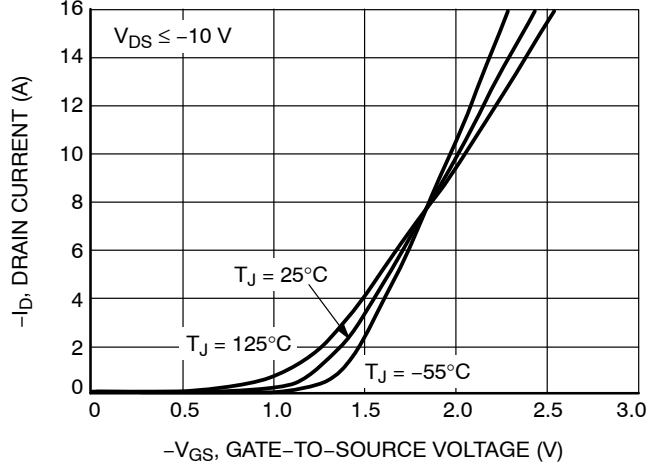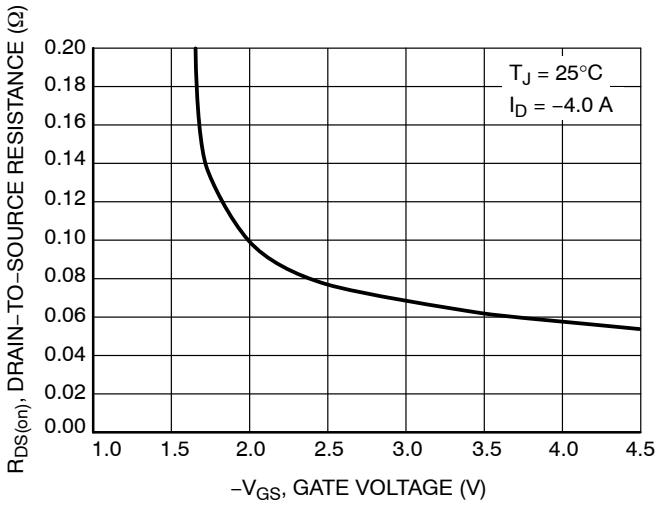**Figure 1. On–Region Characteristics**

Figure 2. Transfer Characteristics

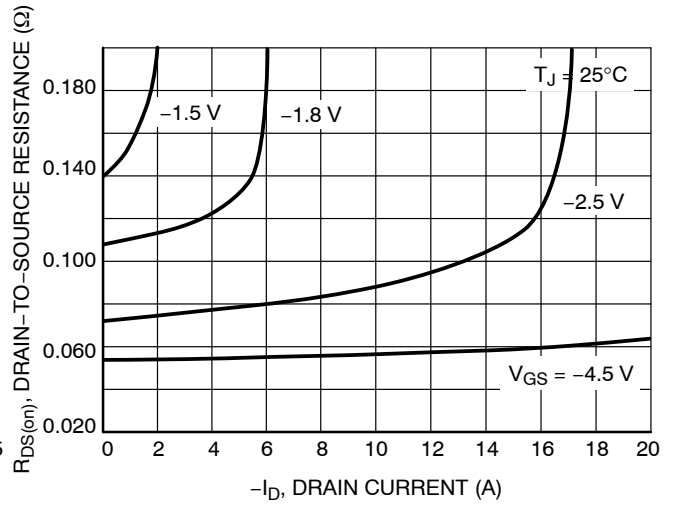**Figure 3. On–Resistance vs. Gate–to–Source Voltage**

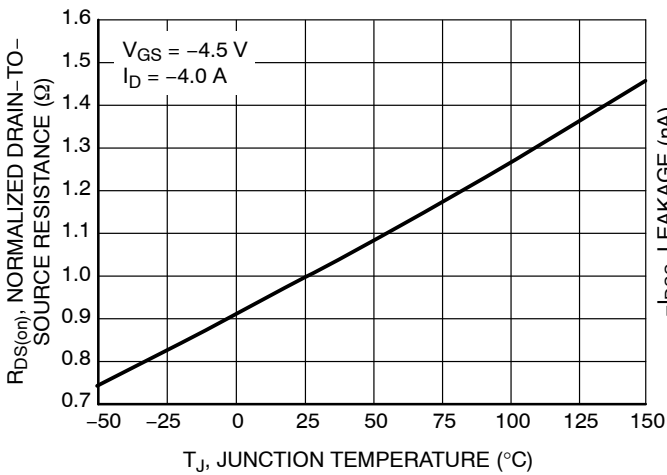**Figure 4. On–Resistance vs. Drain Current and Gate Voltage**

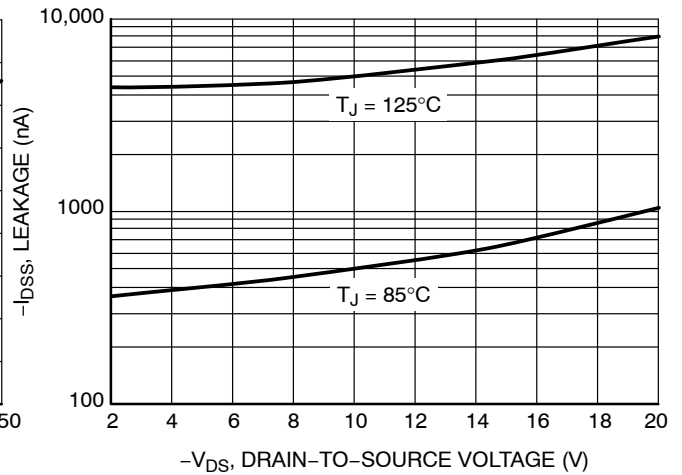**Figure 5. On–Resistance Variation with Temperature**

Figure 6. Drain–to–Source Leakage Current vs. Voltage
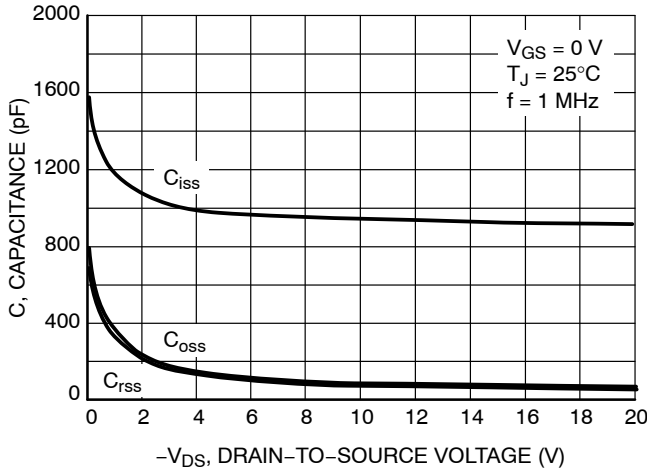
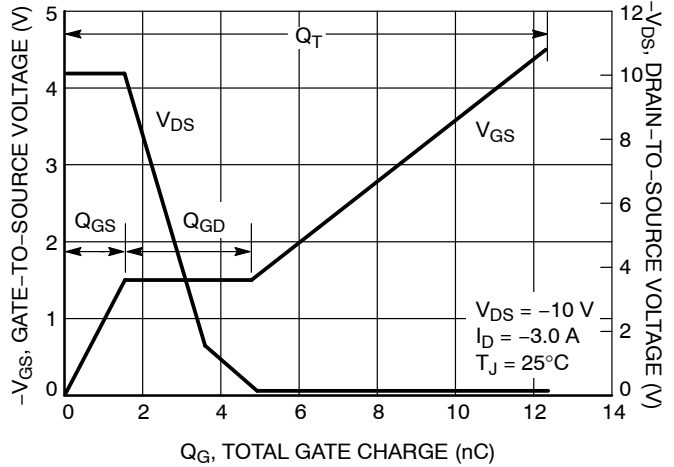## TYPICAL CHARACTERISTICS

Figure 7. Capacitance Variation

Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge
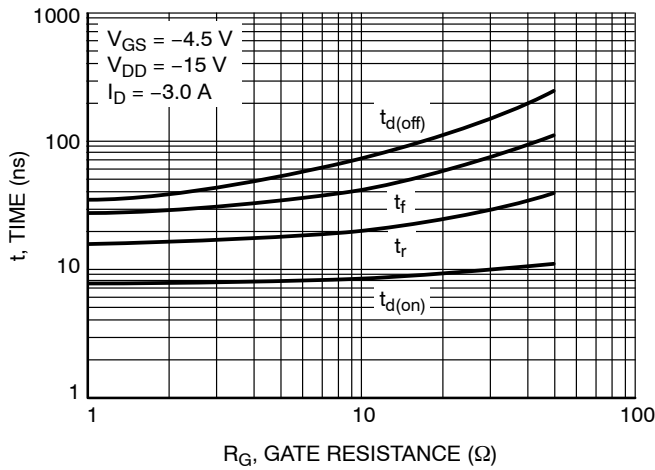
Figure 9. Resistive Switching Time Variation vs. Gate Resistance
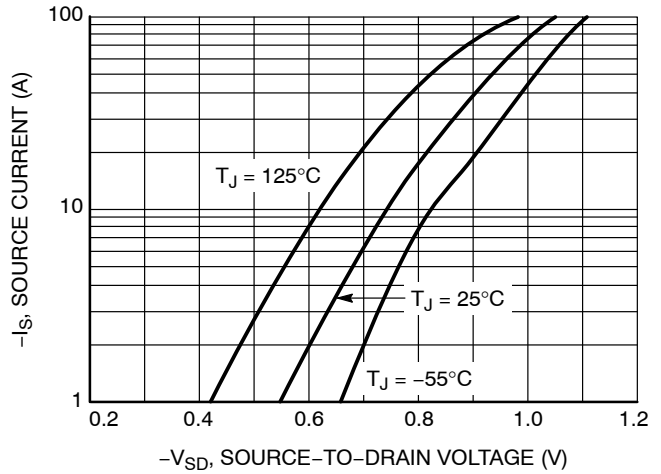
Figure 10. Diode Forward Voltage vs. Current
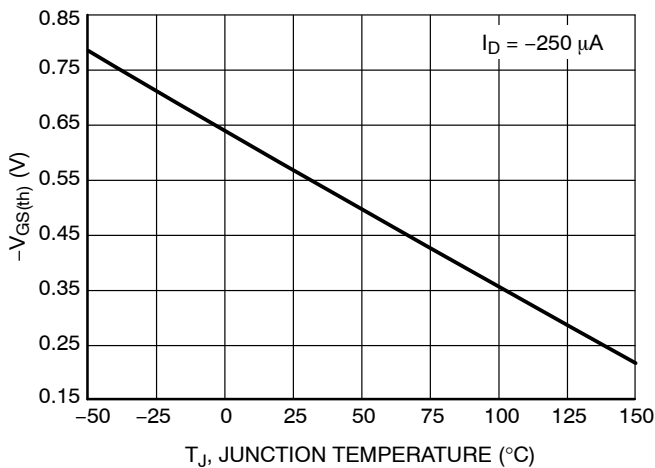
Figure 11. Threshold Voltage
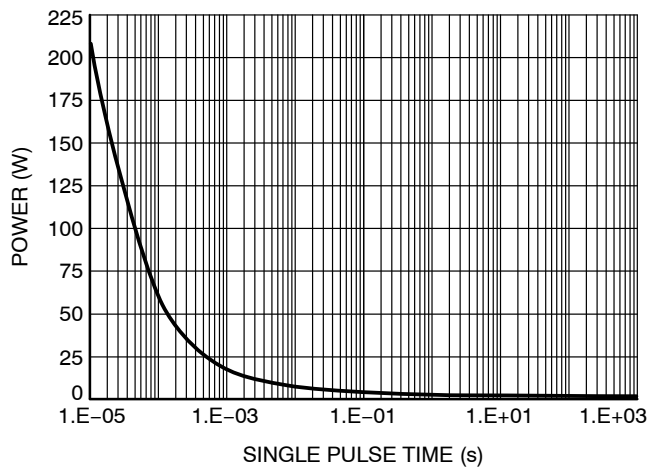
Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS

Figure 13. Maximum Rated Forward Biased Safe Operating Area
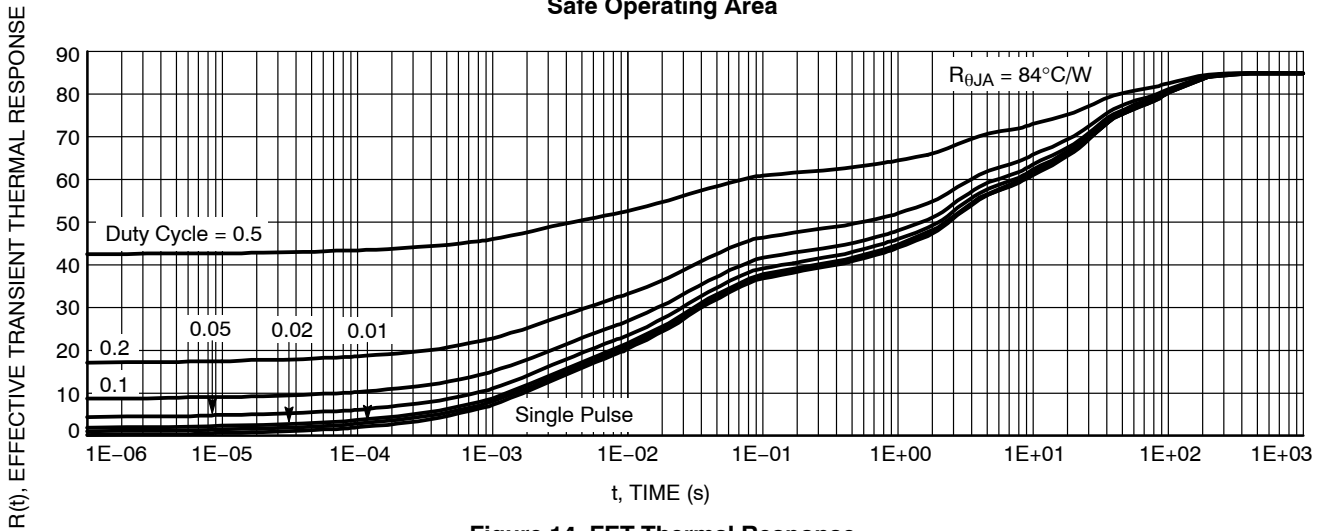
Figure 14. FET Thermal Response

DEVICE ORDERING INFORMATION

Device	Package	Shipping[†]
NTLUS3A90PZTAG	UDFN6 (Pb–Free)	3000 / Tape & Reel
NTLUS3A90PZTBG	UDFN6 (Pb–Free)	3000 / Tape & Reel

μCool is a trademark of Semiconductor Components Industries, LLC (SCILLC).

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

UDFN6 1.6x1.6, 0.5P
CASE 517AU–01
ISSUE O

DATE 16 OCT 2008

SCALE 4:1

6

1

2X | △ | 0.10 | C |

PIN ONE
REFERENCE

2X | △ | 0.10 | C |

D | A
| B

E

TOP VIEW

| // | 0.05 | C |

DETAIL B

A

(A3)

| △ | 0.05 | C |

A1

NOTE 4

SIDE VIEW

C SEATING
PLANE

L | L1

DETAIL A
OPTIONAL
CONSTRUCTION

EXPOSED Cu | MOLD CMPD

A3

A1

DETAIL B
OPTIONAL
CONSTRUCTION
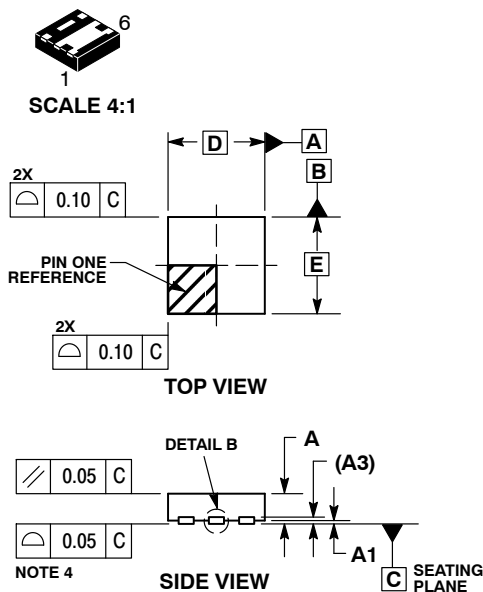
NOTES:
1. DIMENSIONING AND TOLERANCING PER
   ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL
   AND IS MEASURED BETWEEN 0.15 AND
   0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED
   PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
---	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.20	0.30
D	1.60 BSC	
E	1.60 BSC	
e	0.50 BSC	
D1	0.62	0.72
D2	0.15	0.25
E2	0.57	0.67
F	0.55 BSC	
G	0.25 BSC	
L	0.20	0.30
L1	---	0.15

| ⊕ | 0.10 | C | A | B |

F

e

D2

1 | 3

G | E2

6X L

| ⊕ | 0.10 | C | A | B |

DETAIL A

6 | 4

D1

6X b

| ⊕ | 0.10 | C | A | B |
| | 0.05 | C | NOTE 3 | |

BOTTOM VIEW

GENERIC
MARKING DIAGRAM*

1 ○
XX M▪
▪
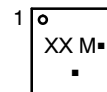
XX = Specific Device Code
M = Date Code
▪ = Pb–Free Package
(Note: Microdot may be in either location)

*This information is generic. Please refer
to device data sheet for actual part
marking.
Pb–Free indicator, "G" or microdot " ▪",
may or may not be present.

SOLDERMASK DEFINED
MOUNTING FOOTPRINT*

0.82

0.16 | 0.43

0.68

2X
0.35

1.90

0.28

1

6X
0.32

0.50 PITCH

DIMENSIONS: MILLIMETERS
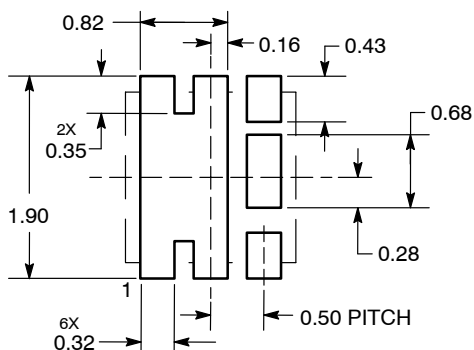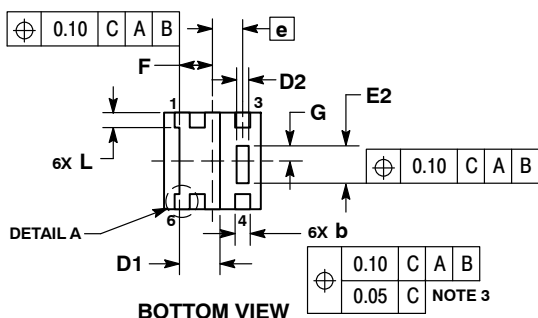
*For additional information on our Pb–Free strategy and soldering
details, please download the ON Semiconductor Soldering and
Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800–282–9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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